

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2022 to Q4/2023

Based on structural similarity

Supplier Nexperia B.V. Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		User Part Number PDTC124ET-Q Part Description											
									Nexperia DHAM Small Signal Bipolar Transistor				
									SMD package				
		Test Conditions	Duration	# Lots	# Quantity	# Rejects							
		<b>" F</b> 4	TEST Pre- and Post-Stress Electrical Test	T. J. 25.00									
		# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below					
# A1	<b>PC</b> Preconditioning	JESD22-A113 Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85% Reflow soldering	24 hours 168 hours 3 cycles	1674	70490	0							
# B1	HTRB High Temperature Reverse Bias	MIL-STD-750-1 M1039 Method A Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage	1000 hours	415	18680	0							
" DI			1000 110013	113	10000	0							
# A4	<b>TC</b> Temperature Cycling	JESD22-A104 -65 °C to Tjmax, not to exceed 150°C	1000 cycles	343	15360	0							
# A3 <b>or</b>	UHAST Unbiased HAST	JESD22-A118 Tamb = 130 °C, RH = 85 %	— 96 hours	362	15920	0							
# A3 alt	<b>AC</b> Autoclave	JESD22-A102 Tamb = 121 °C, RH = 100 % Pressure = 205 kPa (29.7 psia)	— 90 Hours	302	13920	Ü							
# A2 alt	<b>H3TRB</b> High Humidity High Temperature Reverse Bias	JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of rated reverse voltage $^{[1]}$	1000 hours	343	15360	0							
# A5	IOL Intermittent Operating Life	MIL-STD-750 Method 1037 ton = toff, devices powered to insure ΔTj = 100 °C for 15000 cycles	1000 hours	343	15360	0							
		,	2000 110013	3 13	13300	<u> </u>							
# C8	<b>RSH</b> Resistance to Solder Heat	JESD22-A111 260 °C ± 5 °C	10 s	283	8490	0							
# C10	<b>SD</b> Solderability	J-STD-002		214	6420	0							

<sup>[1]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	18680	0	0,23	4,40E+09

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